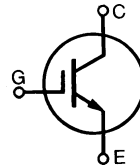


Low $V_{CE(sat)}$ IGBT High Speed IGBT

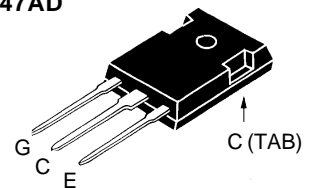
IXGH 12N100
IXGH 12N100A

V_{CES}	I_{C25}	$V_{CE(sat)}$
1000 V	24 A	3.5 V
1000 V	24 A	4.0 V



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	1000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	24	A
I_{C90}	$T_C = 90^\circ\text{C}$	12	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	48	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 150\ \Omega$ Clamped inductive load, $L = 300\ \mu\text{H}$	$I_{CM} = 24$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247AD



G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 3\text{ mA}$, $V_{GE} = 0\text{ V}$ BV_{CES} temperature coefficient	1000	0.072	V %/K
$V_{GE(th)}$	$I_C = 500\ \mu\text{A}$, $V_{GE} = V_{GE}$ $V_{GE(th)}$ temperature coefficient	2.5	-0.192	V %/K
I_{CES}	$V_{CE} = 0.8 V_{CES}$, $T_J = 25^\circ\text{C}$ $V_{GE} = 0\text{ V}$, $T_J = 125^\circ\text{C}$			250 μA 1 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$	12N100 12N100A		3.5 V 4.0 V

Features

- International standard package JEDEC TO-247 AD
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
- for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
- drive simplicity
- Voltage rating guaranteed at high temperature (125°C)

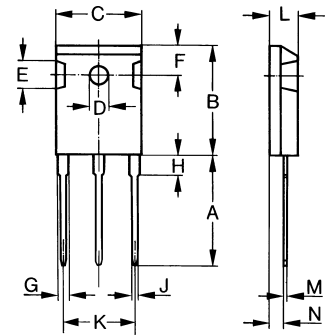
Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	6	10	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		750	pF
C_{oes}			80	pF
C_{res}			30	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		65	90 nC
Q_{ge}			8	nC
Q_{gc}			24	45 nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\ \mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 120\ \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, higher T_J or increased R_G		100	ns
t_{ri}			200	ns
$t_{d(off)}$			850	1000 ns
t_{fi}		12N100	800	1000 ns
		12N100A	500	700 ns
E_{off}		12N100	2.5	mJ
		12N100A	1.5	3.0 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\ \mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 120\ \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, higher T_J or increased R_G		100	ns
t_{ri}			200	ns
E_{on}			1.1	mJ
$t_{d(off)}$			900	ns
t_{fi}		12N100	1250	ns
	12N100A	950	ns	
E_{off}		12N100	3.5	mJ
		12N100A	2.2	mJ
R_{thJC}			1.25	K/W
R_{thCK}		0.25		K/W

TO-247 AD (IXGH) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

IXGH12N100/A characteristic curves may be found in the IXGH12N100U/AU1 data sheet.